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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	C166SV2
Core Size	16-Bit
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I ² C, LINbus, SPI, SSC, UART/USART, USI
Peripherals	I ² S, POR, PWM, WDT
Number of I/O	76
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 11x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP Exposed Pad
Supplier Device Package	PG-LQFP-100-8
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/sak-xe164gm-24f80l-aa

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2.1 Pin Configuration and Definition

The pins of the XE164xM are described in detail in [Table 5](#), which includes all alternate functions. For further explanations please refer to the footnotes at the end of the table. The following figure summarizes all pins, showing their locations on the four sides of the package.

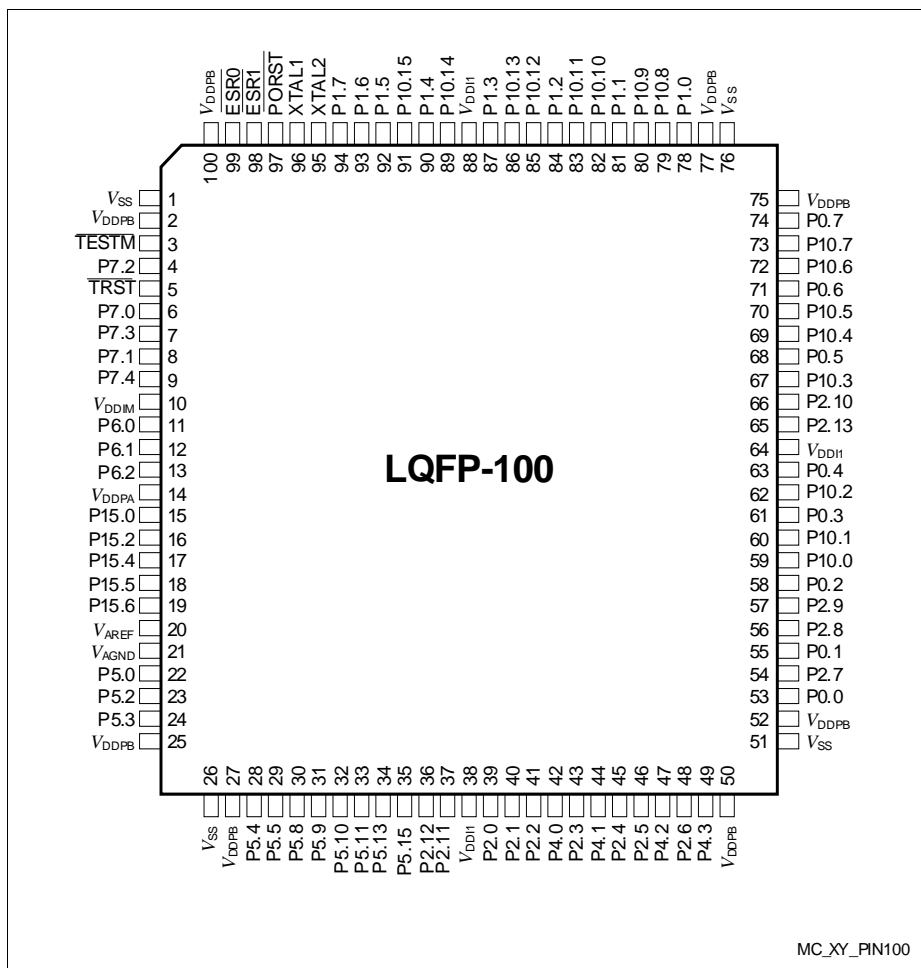


Figure 3 XE164xM Pin Configuration (top view)

Table 5 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Type	Function
97	PORST	I	In/B	Power On Reset Input A low level at this pin resets the XE164xM completely. A spike filter suppresses input pulses <10 ns. Input pulses >100 ns safely pass the filter. The minimum duration for a safe recognition should be 120 ns. An internal pull-up device will hold this pin high when nothing is driving it.
98	ESR1	O0 / I	St/B	External Service Request 1 After power-up, an internal weak pull-up device holds this pin high when nothing is driving it.
	RxDC0E	I	St/B	CAN Node 0 Receive Data Input
	U1C0_DX0F	I	St/B	USIC1 Channel 0 Shift Data Input
	U1C0_DX2C	I	St/B	USIC1 Channel 0 Shift Control Input
	U1C1_DX0C	I	St/B	USIC1 Channel 1 Shift Data Input
	U1C1_DX2B	I	St/B	USIC1 Channel 1 Shift Control Input
	U2C1_DX2C	I	St/B	USIC2 Channel 1 Shift Control Input
99	ESR0	O0 / I	St/B	External Service Request 0 After power-up, ESR0 operates as open-drain bidirectional reset with a weak pull-up.
	U1C0_DX0E	I	St/B	USIC1 Channel 0 Shift Data Input
	U1C0_DX2B	I	St/B	USIC1 Channel 0 Shift Control Input
10	V _{DDIM}	-	PS/M	Digital Core Supply Voltage for Domain M Decouple with a ceramic capacitor, see Data Sheet for details.
38, 64, 88	V _{DDI1}	-	PS/I	Digital Core Supply Voltage for Domain 1 Decouple with a ceramic capacitor, see Data Sheet for details. All V _{DDI1} pins must be connected to each other.
14	V _{DDPA}	-	PS/A	Digital Pad Supply Voltage for Domain A Connect decoupling capacitors to adjacent V _{DDP} /V _{SS} pin pairs as close as possible to the pins. <i>Note: The A/D Converters and ports P5, P6 and P15 are fed from supply voltage V_{DDPA}.</i>

Functional Description

Table 8 Compare Modes (cont'd)

Compare Modes	Function
Mode 2	Interrupt-only compare mode; Only one compare interrupt per timer period is generated
Mode 3	Pin set '1' on match; pin reset '0' on compare timer overflow; Only one compare event per timer period is generated
Double Register Mode	Two registers operate on one pin; Pin toggles on each compare match; Several compare events per timer period are possible
Single Event Mode	Generates single edges or pulses; Can be used with any compare mode

3.18 Parallel Ports

The XE164xM provides up to 76 I/O lines which are organized into 7 input/output ports and 2 input ports. All port lines are bit-addressable, and all input/output lines can be individually (bit-wise) configured via port control registers. This configuration selects the direction (input/output), push/pull or open-drain operation, activation of pull devices, and edge characteristics (shape) and driver characteristics (output current) of the port drivers. The I/O ports are true bidirectional ports which are switched to high impedance state when configured as inputs. During the internal reset, all port pins are configured as inputs without pull devices active.

All port lines have alternate input or output functions associated with them. These alternate functions can be programmed to be assigned to various port pins to support the best utilization for a given application. For this reason, certain functions appear several times in [Table 9](#).

All port lines that are not used for alternate functions may be used as general purpose I/O lines.

Table 9 Summary of the XE164xM's Ports

Port	Width	I/O	Connected Modules
P0	8	I/O	EBC (A7...A0), CCU6, USIC, CAN
P1	8	I/O	EBC (A15...A8), CCU6, USIC
P2	14	I/O	EBC (READY, $\overline{\text{BHE}}$, A23...A16, AD15...AD13, D15...D13), CAN, CC2, GPT12E, USIC, DAP/JTAG
P4	4	I/O	EBC ($\overline{\text{CS3}}$... $\overline{\text{CS0}}$), CC2, CAN, GPT12E, USIC
P5	11	I	Analog Inputs, CCU6, DAP/JTAG, GPT12E, CAN
P6	3	I/O	ADC, CAN, GPT12E
P7	5	I/O	CAN, GPT12E, SCU, DAP/JTAG, CCU6, ADC, USIC
P10	16	I/O	EBC (ALE, $\overline{\text{RD}}$, $\overline{\text{WR}}$, AD12...AD0, D12...D0), CCU6, USIC, DAP/JTAG, CAN
P15	5	I	Analog Inputs, GPT12E

Functional Description

Table 10 Instruction Set Summary (cont'd)

Mnemonic	Description	Bytes
ROL/ROR	Rotate left/right direct word GPR	2
ASHR	Arithmetic (sign bit) shift right direct word GPR	2
MOV(B)	Move word (byte) data	2 / 4
MOVBS/Z	Move byte operand to word op. with sign/zero extension	2 / 4
JMPA/I/R	Jump absolute/indirect/relative if condition is met	4
JMPS	Jump absolute to a code segment	4
JB(C)	Jump relative if direct bit is set (and clear bit)	4
JNB(S)	Jump relative if direct bit is not set (and set bit)	4
CALLA/I/R	Call absolute/indirect/relative subroutine if condition is met	4
CALLS	Call absolute subroutine in any code segment	4
PCALL	Push direct word register onto system stack and call absolute subroutine	4
TRAP	Call interrupt service routine via immediate trap number	2
PUSH/POP	Push/pop direct word register onto/from system stack	2
SCXT	Push direct word register onto system stack and update register with word operand	4
RET(P)	Return from intra-segment subroutine (and pop direct word register from system stack)	2
RETS	Return from inter-segment subroutine	2
RETI	Return from interrupt service subroutine	2
SBRK	Software Break	2
SRST	Software Reset	4
IDLE	Enter Idle Mode	4
PWRDN	Unused instruction ¹⁾	4
SRVWDT	Service Watchdog Timer	4
DISWDT/ENWDT	Disable/Enable Watchdog Timer	4
EINIT	End-of-Initialization Register Lock	4
ATOMIC	Begin ATOMIC sequence	2
EXTR	Begin EXTENDED Register sequence	2
EXTP(R)	Begin EXTENDED Page (and Register) sequence	2 / 4
EXTS(R)	Begin EXTENDED Segment (and Register) sequence	2 / 4

Functional Description

Table 10 Instruction Set Summary (cont'd)

Mnemonic	Description	Bytes
NOP	Null operation	2
CoMUL/CoMAC	Multiply (and accumulate)	4
CoADD/CoSUB	Add/Subtract	4
Co(A)SHR	(Arithmetic) Shift right	4
CoSHL	Shift left	4
CoLOAD/STORE	Load accumulator/Store MAC register	4
CoCMP	Compare	4
CoMAX/MIN	Maximum/Minimum	4
CoABS/CoRND	Absolute value/Round accumulator	4
CoMOV	Data move	4
CoNEG/NOP	Negate accumulator/Null operation	4

- 1) The Enter Power Down Mode instruction is not used in the XE164xM, due to the enhanced power control scheme. PWRDN will be correctly decoded, but will trigger no action.

4.1.2 Operating Conditions

The following operating conditions must not be exceeded to ensure correct operation of the XE164xM. All parameters specified in the following sections refer to these operating conditions, unless otherwise noticed.

Note: Typical parameter values refer to room temperature and nominal supply voltage, minimum/maximum parameter values also include conditions of minimum/maximum temperature and minimum/maximum supply voltage. Additional details are described where applicable.

Table 12 Operating Conditions

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Voltage Regulator Buffer Capacitance for DMP_M	C_{EVRM} SR	1.0	—	4.7	μF	1)
Voltage Regulator Buffer Capacitance for DMP_1	C_{EVR1} SR	0.47	—	2.2	μF	1)2)
External Load Capacitance	C_L SR	—	20 ³⁾	—	pF	pin out driver= default 4)
System frequency	f_{SYS} SR	—	—	100	MHz	5)
Overload current for analog inputs ⁶⁾	I_{OVA} SR	-2	—	5	mA	not subject to production test
Overload current for digital inputs ⁶⁾	I_{OVD} SR	-5	—	5	mA	not subject to production test
Overload current coupling factor for analog inputs ⁷⁾	K_{OVA} CC	—	2.5×10^{-4}	1.5×10^{-3}	-	$I_{OV} < 0$ mA; not subject to production test
		—	1.0×10^{-6}	1.0×10^{-4}	-	$I_{OV} > 0$ mA; not subject to production test
Overload current coupling factor for digital I/O pins	K_{OVD} CC	—	1.0×10^{-2}	3.0×10^{-2}		$I_{OV} < 0$ mA; not subject to production test
		—	1.0×10^{-4}	5.0×10^{-3}		$I_{OV} > 0$ mA; not subject to production test

Electrical Parameters

Table 12 Operating Conditions (cont'd)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Absolute sum of overload currents	$\Sigma I_{OV} $ SR	—	—	50	mA	not subject to production test
Digital core supply voltage for domain M ⁸⁾	V_{DDIM} CC	—	1.5	—		
Digital core supply voltage for domain 1 ⁸⁾	V_{DDI1} CC	—	1.5	—		
Digital supply voltage for IO pads and voltage regulators	V_{DDP} SR	4.5	—	5.5	V	
Digital ground voltage	V_{SS} SR	—	0	—	V	

- 1) To ensure the stability of the voltage regulators the EVRs must be buffered with ceramic capacitors. Separate buffer capacitors with the recommended values shall be connected as close as possible to each V_{DDIM} and V_{DDI1} pin to keep the resistance of the board tracks below 2 Ohm. Connect all V_{DDI1} pins together. The minimum capacitance value is required for proper operation under all conditions (e.g. temperature). Higher values slightly increase the startup time.
- 2) Use one Capacitor for each pin.
- 3) This is the reference load. For bigger capacitive loads, use the derating factors listed in the PAD properties section.
- 4) The timing is valid for pin drivers operating in default current mode (selected after reset). Reducing the output current may lead to increased delays or reduced driving capability (C_L).
- 5) The operating frequency range may be reduced for specific device types. This is indicated in the device designation (...FxxL). 80 MHz devices are marked ...F80L.
- 6) Overload conditions occur if the standard operating conditions are exceeded, i.e. the voltage on any pin exceeds the specified range: $V_{OV} > V_{IHmax}$ ($I_{OV} > 0$) or $V_{OV} < V_{ILmin}$ ($I_{OV} < 0$). The absolute sum of input overload currents on all pins may not exceed 50 mA. The supply voltages must remain within the specified limits. Proper operation under overload conditions depends on the application. Overload conditions must not occur on pin XTAL1 (powered by V_{DDIM}).
- 7) An overload current (I_{OV}) through a pin injects a certain error current (I_{INj}) into the adjacent pins. This error current adds to the respective pins leakage current (I_{OZ}). The amount of error current depends on the overload current and is defined by the overload coupling factor K_{OV} . The polarity of the injected error current is inverse compared to the polarity of the overload current that produces it. The total current through a pin is $|I_{TOT}| = |I_{OZ}| + (|I_{OV}| \cdot K_{OV})$. The additional error current may distort the input voltage on analog inputs.
- 8) Value is controlled by on-chip regulator

Pullup/Pulldown Device Behavior

Most pins of the XE164xM feature pullup or pulldown devices. For some special pins these are fixed; for the port pins they can be selected by the application.

The specified current values indicate how to load the respective pin depending on the intended signal level. **Figure 13** shows the current paths.

The shaded resistors shown in the figure may be required to compensate system pull currents that do not match the given limit values.

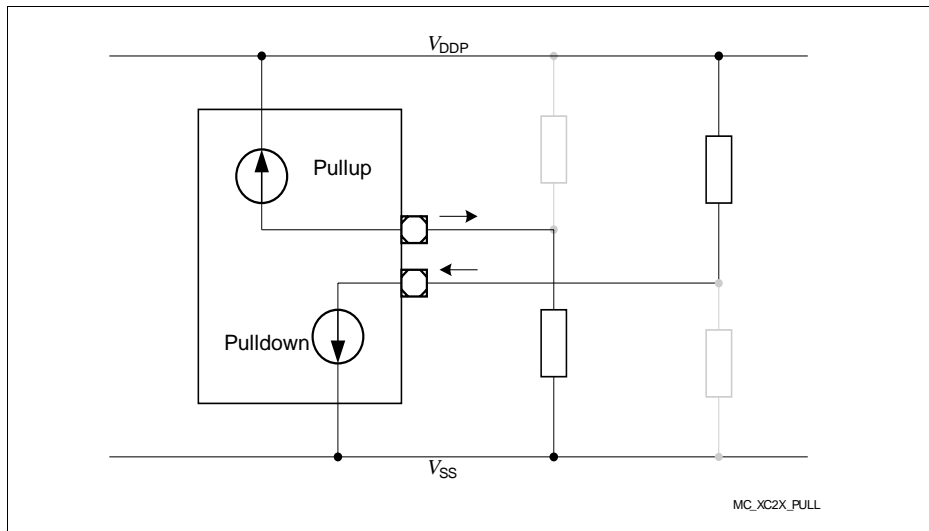


Figure 13 Pullup/Pulldown Current Definition

4.5 Flash Memory Parameters

The XE164xM is delivered with all Flash sectors erased and with no protection installed. The data retention time of the XE164xM's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 22 Flash Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Parallel Flash module program/erase limit depending on Flash read activity	N_{PP} SR	–	–	4 ¹⁾		$N_{FL_RD} \leq 1$, $f_{SYS} \leq 80$ MHz
		–	–	1 ²⁾		$N_{FL_RD} > 1$
Flash erase endurance for security pages	N_{SEC} SR	10	–	–	cycle s	$t_{RET} \geq 20$ years
Flash wait states ³⁾	N_{WSFLAS} H SR	1	–	–		$f_{SYS} \leq 8$ MHz
		2	–	–		$f_{SYS} \leq 13$ MHz
		3	–	–		$f_{SYS} \leq 17$ MHz
		4	–	–		$f_{SYS} > 17$ MHz
Erase time per sector/page	t_{ER} CC	–	7 ⁴⁾	8.0	ms	
Programming time per page	t_{PR} CC	–	3 ⁴⁾	3.5	ms	
Data retention time	t_{RET} CC	20	–	–	year s	$N_{Er} \leq 1\,000$ cycles
Drain disturb limit	N_{DD} SR	32	–	–	cycle s	

4.6 AC Parameters

These parameters describe the dynamic behavior of the XE164xM.

4.6.1 Testing Waveforms

These values are used for characterization and production testing (except pin XTAL1).

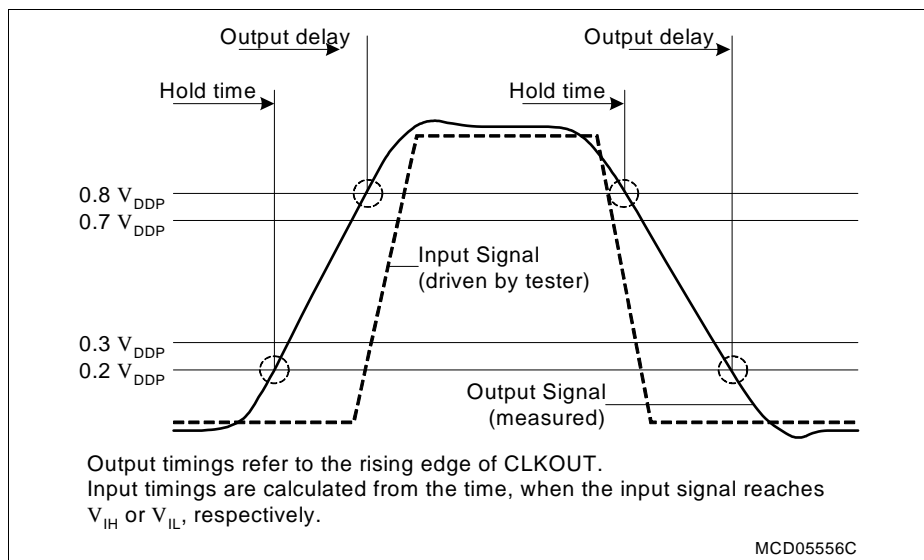


Figure 17 Input Output Waveforms

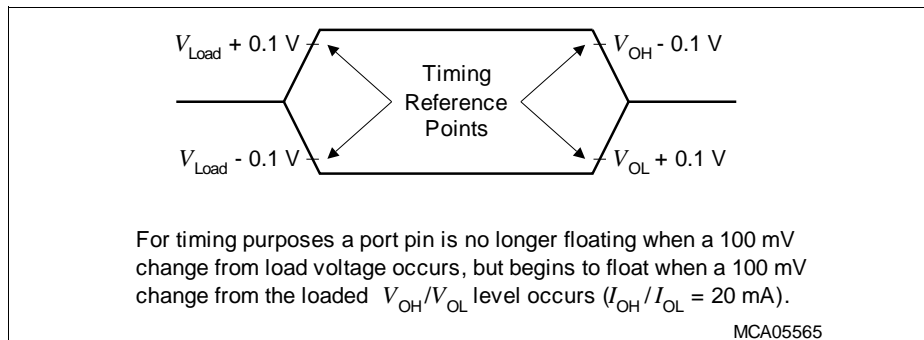


Figure 18 Floating Waveforms

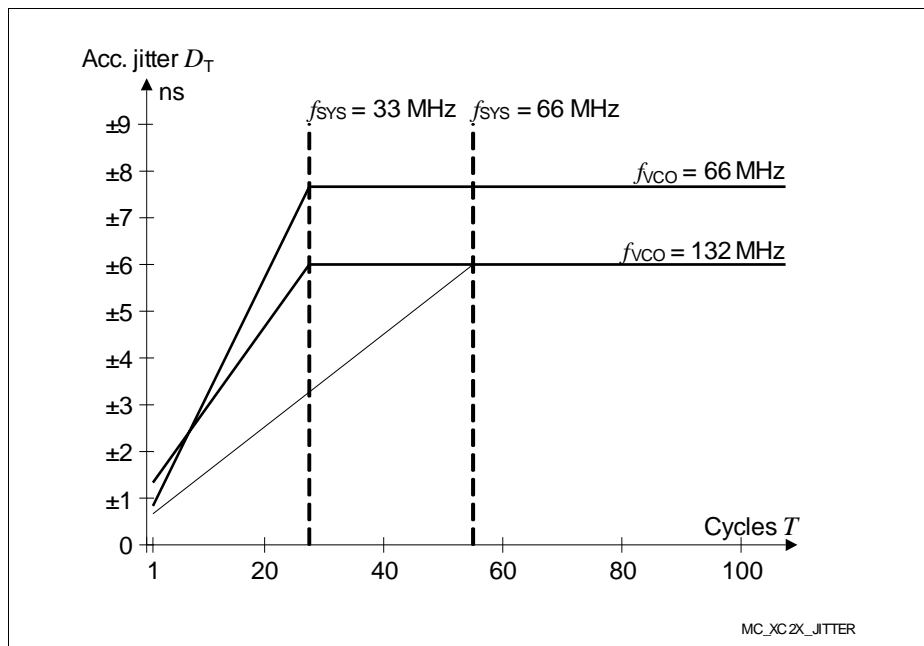


Figure 20 Approximated Accumulated PLL Jitter

Note: The specified PLL jitter values are valid if the capacitive load per pin does not exceed $C_L = 20 \text{ pF}$.

The maximum peak-to-peak noise on the pad supply voltage (measured between V_{DDPB} pin 100 and V_{SS} pin 1) is limited to a peak-to-peak voltage of $V_{PP} = 50 \text{ mV}$. This can be achieved by appropriate blocking of the supply voltage as close as possible to the supply pins and using PCB supply and ground planes.

Electrical Parameters

- 1) The amplitude voltage V_{AX1} refers to the offset voltage V_{OFF} . This offset voltage must be stable during the operation and the resulting voltage peaks must remain within the limits defined by V_{IX1} .
- 2) Overload conditions must not occur on pin XTAL1.

Note: For crystal or ceramic resonator operation, it is strongly recommended to measure the oscillation allowance (negative resistance) in the final target system (layout) to determine the optimum parameters for oscillator operation.

The manufacturers of crystals and ceramic resonators offer an oscillator evaluation service. This evaluation checks the crystal/resonator specification limits to ensure a reliable oscillator operation.

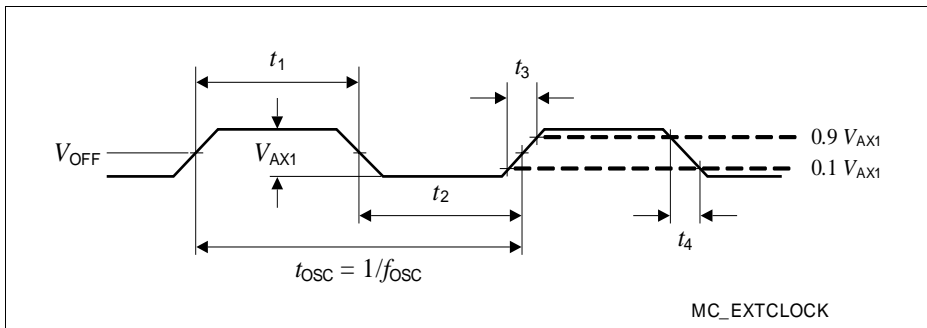


Figure 21 External Clock Drive XTAL1

4.6.4 Pad Properties

The output pad drivers of the XE164xM can operate in several user-selectable modes. Strong driver mode allows controlling external components requiring higher currents such as power bridges or LEDs. Reducing the driving power of an output pad reduces electromagnetic emissions (EME). In strong driver mode, selecting a slower edge reduces EME.

The dynamic behavior, i.e. the rise time and fall time, depends on the applied external capacitance that must be charged and discharged. Timing values are given for a capacitance of 20 pF, unless otherwise noted.

In general, the performance of a pad driver depends on the available supply voltage V_{DDP} . The following table lists the pad parameters.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 26 is valid under the following conditions:

$V_{DDP} \geq 3.0 \text{ V}$; $V_{DDP_{typ}} = 3.3 \text{ V}$; $V_{DDP} \leq 4.5 \text{ V}$; $C_L \geq 20 \text{ pF}$; $C_L \leq 100 \text{ pF}$;

Table 26 Standard Pad Parameters for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Maximum output driver current (absolute value) ¹⁾	I_{Omax} CC	—	—	10	mA	Strong driver
		—	—	2.5	mA	Medium driver
		—	—	0.5	mA	Weak driver
Nominal output driver current (absolute value)	I_{Onom} CC	—	—	2.5	mA	Strong driver
		—	—	1.0	mA	Medium driver
		—	—	0.1	mA	Weak driver
Rise and Fall times (10% - 90%)	t_{RF} CC	—	—	$6.2 + 0.24 \times C_L$	ns	Strong driver; Sharp edge
		—	—	$24 + 0.3 \times C_L$	ns	Strong driver; Medium edge
		—	—	$34 + 0.3 \times C_L$	ns	Strong driver; Slow edge
		—	—	$37 + 0.65 \times C_L$	ns	Medium driver
		—	—	$500 + 2.5 \times C_L$	ns	Weak driver

1) The total output current that may be drawn at a given time must be limited to protect the supply rails from damage. For any group of 16 neighboring output pins, the total output current in each direction (ΣI_{OL} and ΣI_{OH}) must remain below 50 mA.

4.6.5 External Bus Timing

The following parameters specify the behavior of the XE164xM bus interface.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Bus Interface Performance Limits

The output frequency at the bus interface pins is limited by the performance of the output drivers. The fast clock driver (used for CLKOUT) can drive 80-MHz signals, the standard drivers can drive 40-MHz signals

Therefore, the speed of the EBC must be limited, either by limiting the system frequency to $f_{SYS} \leq 80$ MHz or by adding waitstates so that signal transitions have a minimum distance of 12.5 ns.

For a description of the bus protocol and the programming of its variable timing parameters, please refer to the User's Manual.

Table 27 EBC Parameters

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
CLKOUT Cycle Time ¹⁾	t_5 CC	—	$1 / f_{SYS}$	—	ns	
CLKOUT high time	t_6 CC	2	—	—		
CLKOUT low time	t_7 CC	2	—	—		
CLKOUT rise time	t_8 CC	—	—	3	ns	
CLKOUT fall time	t_9 CC	—	—	3		

1) The CLKOUT cycle time is influenced by PLL jitter. For longer periods the relative deviation decreases (see PLL deviation formula).

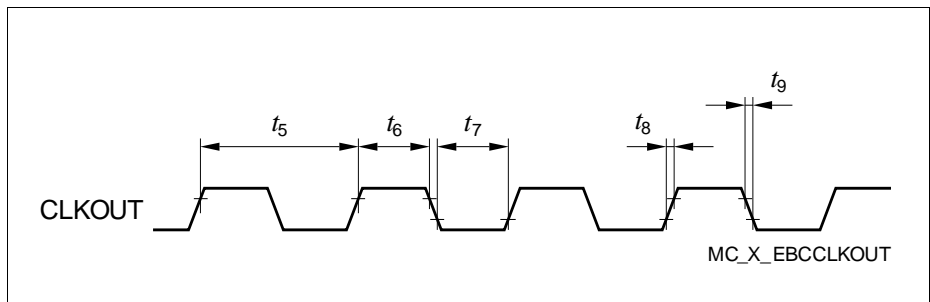


Figure 22 CLKOUT Signal Timing

Debug via JTAG

The following parameters are applicable for communication through the JTAG debug interface. The JTAG module is fully compliant with IEEE1149.1-2000.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply; $C_L = 20$ pF.

Table 37 JTAG Interface Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK clock period	t_1 SR	50 ¹⁾	—	—	ns	2)
TCK high time	t_2 SR	16	—	—	ns	
TCK low time	t_3 SR	16	—	—	ns	
TCK clock rise time	t_4 SR	—	—	8	ns	
TCK clock fall time	t_5 SR	—	—	8	ns	
TDI/TMS setup to TCK rising edge	t_6 SR	6	—	—	ns	
TDI/TMS hold after TCK rising edge	t_7 SR	6	—	—	ns	
TDO valid from TCK falling edge (propagation delay) ³⁾	t_8 CC	—	25	29	ns	
TDO high impedance to valid output from TCK falling edge ⁴⁾³⁾	t_9 CC	—	25	29	ns	
TDO valid output to high impedance from TCK falling edge ³⁾	t_{10} CC	—	25	29	ns	
TDO hold after TCK falling edge ³⁾	t_{18} CC	5	—	—	ns	

1) The debug interface cannot operate faster than the overall system, therefore $t_1 \geq t_{sys}$.

2) Under typical conditions, the interface can operate at transfer rates up to 20 MHz.

3) The falling edge on TCK is used to generate the TDO timing.

4) The setup time for TDO is given implicitly by the TCK cycle time.

Table 38 JTAG Interface Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
TCK clock period	t_1 SR	50 ¹⁾	—	—	ns	2)
TCK high time	t_2 SR	16	—	—	ns	
TCK low time	t_3 SR	16	—	—	ns	
TCK clock rise time	t_4 SR	—	—	8	ns	
TCK clock fall time	t_5 SR	—	—	8	ns	
TDI/TMS setup to TCK rising edge	t_6 SR	6	—	—	ns	
TDI/TMS hold after TCK rising edge	t_7 SR	6	—	—	ns	
TDO valid from TCK falling edge (propagation delay) ³⁾	t_8 CC	—	32	36	ns	
TDO high impedance to valid output from TCK falling edge ⁴⁾³⁾	t_9 CC	—	32	36	ns	
TDO valid output to high impedance from TCK falling edge ³⁾	t_{10} CC	—	32	36	ns	
TDO hold after TCK falling edge ³⁾	t_{18} CC	5	—	—	ns	

1) The debug interface cannot operate faster than the overall system, therefore $t_1 \geq t_{SYS}$.

2) Under typical conditions, the interface can operate at transfer rates up to 20 MHz.

3) The falling edge on TCK is used to generate the TDO timing.

4) The setup time for TDO is given implicitly by the TCK cycle time.

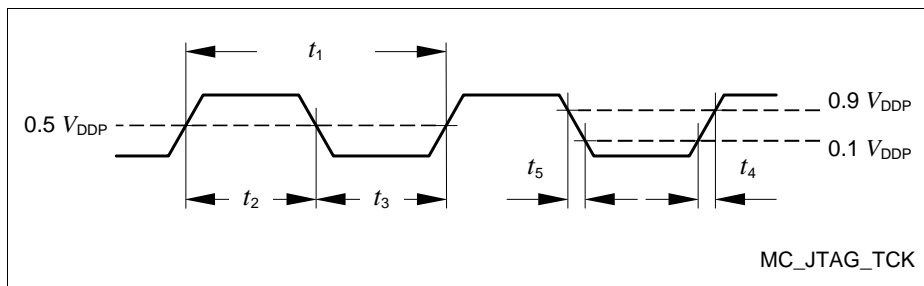


Figure 30 Test Clock Timing (TCK)

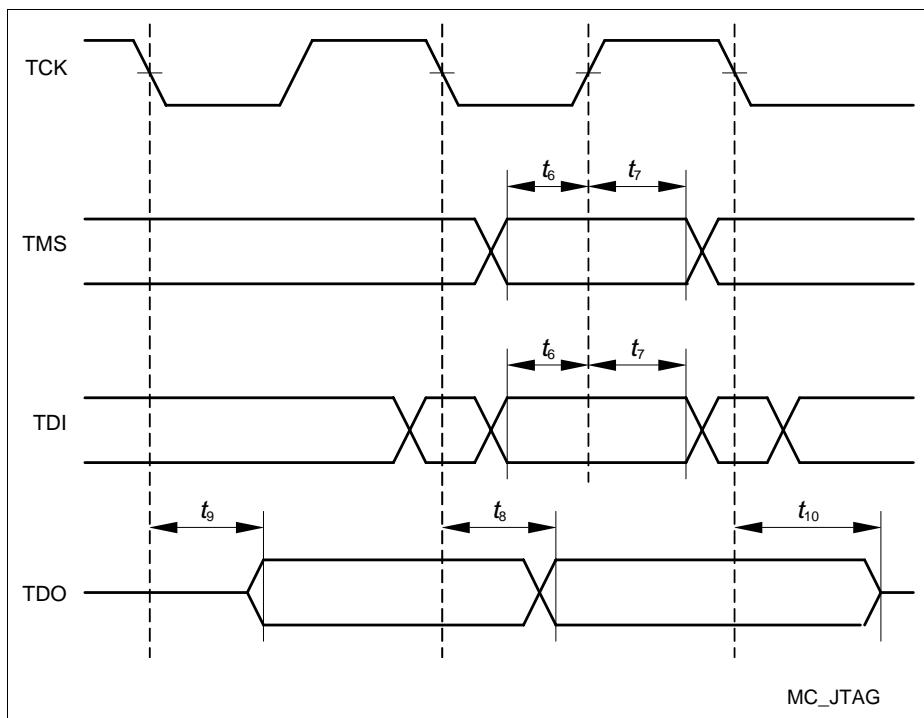


Figure 31 JTAG Timing